Yasuhiko Arakawa

List of Publications by Year in Descending Order

626 papers	22,186 citations	66 h-index	128 g-index
671 ext. papers	25,014 ext. citations	3.3 avg, IF	6.87 L-index

#	Paper	IF	Citations
626	InAs/InGaAs quantum dot lasers on multi-functional metamorphic buffer layers: erratum.. *Optics Express*, **2022**, 30, 6617	3.3	
625	Impact of Quantum Dots on III-Nitride Lasers: A Theoretical Calculation on Linewidth Enhancement Factors. *IEEE Journal of Selected Topics in Quantum Electronics*, **2022**, 28, 1-7	3.8	
624	A large-scale single-mode array laser based on a topological edge mode. *Nanophotonics*, **2022**,	6.3	2
623	Unidirectional output from a quantum-dot single-photon source hybrid integrated on silicon. *Optics Express*, **2021**, 29, 37117-37127	3.3	5
622	The heat is on: towards the realization of non-cryogenic photonic quantum technologies. *Materials for Quantum Technology*, **2021**, 1, 013001		3
621	Enhanced Single-Photon Emission from GaN Quantum Dots in Bullseye Structures. *ACS Photonics*, **2021**, 8, 1656-1661	6.3	11
620	E-band InAs quantum dot laser on InGaAs metamorphic buffer layer with filter layer. *Electronics Letters*, **2021**, 57, 567	1.1	2
619	Experimental demonstration of topological slow light waveguides in valley photonic crystals. *Optics Express*, **2021**, 29, 13441-13450	3.3	7
618	Microcavity-based generation of full Poincar beams with arbitrary skyrmion numbers. *Physical Review Research*, **2021**, 3,	3.9	10
617	Evaluation of degradation behavior in quantum dot light-emitting diode with different hole transport materials via transient electroluminescence. *Applied Physics Letters*, **2021**, 118, 203503	3.4	4
616	Pure single-photon emission from an InGaN/GaN quantum dot. *APL Materials*, **2021**, 9, 061106	5.7	5
615	Classification of in situ reflection high energy electron diffraction images by principal component analysis. *Japanese Journal of Applied Physics*, **2021**, 60, SBBK03	1.4	2
614	Recent progress in topological waveguides and nanocavities in a semiconductor photonic crystal platform [Invited]. *Optical Materials Express*, **2021**, 11, 319	2.6	15
613	Photoelectrochemical investigation of charge injection efficiency for quantum dot light-emitting diode. *Applied Physics Letters*, **2021**, 118, 063505	3.4	5
612	GaAs-based microelectromechanical terahertz bolometers fabricated on high-resistivity Si substrates using wafer bonding technique. *Applied Physics Letters*, **2021**, 119, 041104	3.4	5
611	InAs/InGaAs Quantum Dot Lasers on Multi-Functional Metamorphic Buffer Layers. *Optics Express*, **2021**, 29, 29378-29386	3.3	1
610	Single photon generation from AlGaN exciton localization centers exhibiting narrow spectral linewidths. *APL Materials*, **2021**, 9, 121106	5.7	0

609	Surface-passivated high-Q GaAs photonic crystal nanocavity with quantum dots. *APL Photonics*, **2020**, 5, 046106	5.2	19
608	Reflectivity of three-dimensional GaAs photonic band-gap crystals of finite thickness. *Physical Review B*, **2020**, 101,	3.3	2
607	Excitation and emission dynamics of a single photon emitting InGaN quantum dot in a photonic horn structure. *Superlattices and Microstructures*, **2020**, 145, 106575	2.8	1
606	Progress in quantum-dot single photon sources for quantum information technologies: A broad spectrum overview. *Applied Physics Reviews*, **2020**, 7, 021309	17.3	66
605	Classification of Reflection High-Energy Electron Diffraction Pattern Using Machine Learning. *Crystal Growth and Design*, **2020**, 20, 5289-5293	3.5	4
604	The 1200 nm-Band InAs/GaAs Quantum Dot Intermixing by Dry Etching and Ion Implantation. *Physica Status Solidi (A) Applications and Materials Science*, **2020**, 217, 1900851	1.6	0
603	Fabrication and optical characterization of photonic crystal nanocavities with electrodes for gate-defined quantum dots. *Japanese Journal of Applied Physics*, **2020**, 59, SGGI05	1.4	2
602	In situ wavelength tuning of quantum-dot single-photon sources integrated on a CMOS-processed silicon waveguide. *Applied Physics Letters*, **2020**, 116, 041103	3.4	12
601	Slow light waveguides in topological valley photonic crystals. *Optics Letters*, **2020**, 45, 2648-2651	3	29
600	Active topological photonics. *Nanophotonics*, **2020**, 9, 547-567	6.3	78
599	High-Density Silicon Photonics Integrated Technology for Photonics-Electronics Convergence System. *The Review of Laser Engineering*, **2020**, 42, 217	0	
598	Emission at 1.6 □m from InAs Quantum Dots in Metamorphic InGaAs Matrix. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900392	1.3	3
597	Single-photon emission from isolated monolayer islands of InGaN. *Light: Science and Applications*, **2020**, 9, 159	16.7	11
596	Quantum dot lasers for silicon photonics. *Semiconductors and Semimetals*, **2019**, 101, 91-138	0.6	6
595	Photoluminescence properties as a function of growth mechanism for GaSb/GaAs quantum dots grown on Ge substrates. *Journal of Applied Physics*, **2019**, 126, 084301	2.5	2
594	III-nitride quantum dots as single photon emitters. *Semiconductor Science and Technology*, **2019**, 34, 033001	2.4	22
593	Observation of sharp emission lines from Zn-doped GaN. *Japanese Journal of Applied Physics*, **2019**, 58, SCCB15	1.4	
592	Single-photon emission from a further confined InGaN/GaN quantum disc via reverse-reaction growth. *Quantum Engineering*, **2019**, 1, e20	4.5	15

591	Elimination of anti-phase boundaries in a GaAs layer directly-grown on an on-axis Si(001) substrate by optimizing an AlGaAs nucleation layer. *Japanese Journal of Applied Physics*, **2019**, 58, SBBE07	1.4	9
590	Single Plasmon Generation in an InAs/GaAs Quantum Dot in a Transfer-Printed Plasmonic Microring Resonator. *ACS Photonics*, **2019**, 6, 1106-1110	6.3	10
589	Strongly Coupled Single-Quantum-Dot□Cavity System Integrated on a CMOS-Processed Silicon Photonic Chip. *Physical Review Applied*, **2019**, 11,	4.3	21
588	Spectral diffusion time scales in InGaN/GaN quantum dots. *Applied Physics Letters*, **2019**, 114, 112109	3.4	16
587	Quantum-dot single-photon source on a CMOS silicon photonic chip integrated using transfer printing. *APL Photonics*, **2019**, 4, 036105	5.2	24
586	Single photon source based on an InGaN quantum dot in a site-controlled optical horn structure. *Applied Physics Letters*, **2019**, 115, 022101	3.4	8
585	Impact of quantum dots on III-nitride lasers: a theoretical calculation of threshold current densities. *Japanese Journal of Applied Physics*, **2019**, 58, SCCC31	1.4	2
584	High-temperature continuous-wave operation of directly grown InAs/GaAs quantum dot lasers on on-axis Si (001). *Optics Express*, **2019**, 27, 2681-2688	3.3	27
583	Spin-dependent directional emission from a quantum dot ensemble embedded in an asymmetric waveguide. *Optics Letters*, **2019**, 44, 3749-3752	3	1
582	Three-dimensional photonic crystal simultaneously integrating a nanocavity laser and waveguides. *Optica*, **2019**, 6, 296	8.6	14
581	Photonic crystal nanocavity based on a topological corner state. *Optica*, **2019**, 6, 786	8.6	141
580	Advances in Quantum Dot Lasers for High Efficiency and High Output Power Operation. *The Review of Laser Engineering*, **2019**, 47, 210	0	
579	Topological Photonic Crystal Nanocavities. *The Review of Laser Engineering*, **2019**, 47, 351	0	
578	Large vacuum Rabi splitting between a single quantum dot and an H0 photonic crystal nanocavity. *Applied Physics Letters*, **2018**, 112, 093101	3.4	20
577	Measurement of the Emission Lifetime of a GaN Interface Fluctuation Quantum Dot by Power Dependent Single Photon Dynamics. *Physica Status Solidi (A) Applications and Materials Science*, **2018**, 215, 1700630	1.6	4
576	All MBE grown InAs/GaAs quantum dot lasers on on-axis Si (001). *Optics Express*, **2018**, 26, 11568-11576	3.3	68
575	Transfer-printed single-photon sources coupled to wire waveguides. *Optica*, **2018**, 5, 691	8.6	44
574	Scheme for media conversion between electronic spin and photonic orbital angular momentum based on photonic nanocavity. *Optics Express*, **2018**, 26, 21219-21234	3.3	5

573	Low-Noise Characteristics on 1.3-μm-Wavelength Quantum-Dot DFB Lasers Under External Optical Feedback **2018**,		5
572	Topological photonic crystal nanocavity laser. *Communications Physics*, **2018**, 1,	5.4	85
571	InAs/GaAs quantum dot infrared photodetectors on on-axis Si (100) substrates. *Electronics Letters*, **2018**, 54, 1395-1397	1.1	6
570	Circularly Polarized Topological Edge States Derived from Optical Weyl Points in Semiconductor-Based Chiral Woodpile Photonic Crystals. *Journal of the Physical Society of Japan*, **2018**, 87, 123401	1.5	8
569	Improvement of single photon emission from InGaN QDs embedded in porous micropillars. *Applied Physics Letters*, **2018**, 113, 101107	3.4	15
568	High-Q nanocavities in semiconductor-based three-dimensional photonic crystals. *Electronics Letters*, **2018**, 54, 305-307	1.1	4
567	Growth of InGaAs/GaAs nanowire-quantum dots on AlGaAs/GaAs distributed Bragg reflectors for laser applications. *Journal of Crystal Growth*, **2017**, 468, 144-148	1.6	10
566	Emission of Linearly Polarized Single Photons from Quantum Dots Contained in Nonpolar, Semipolar, and Polar Sections of Pencil-Like InGaN/GaN Nanowires. *ACS Photonics*, **2017**, 4, 657-664	6.3	38
565	Ultraclean Single Photon Emission from a GaN Quantum Dot. *Nano Letters*, **2017**, 17, 2902-2907	11.5	59
564	Optical coupling between atomically thin black phosphorus and a two dimensional photonic crystal nanocavity. *Applied Physics Letters*, **2017**, 110, 223105	3.4	11
563	Demonstration of lasing oscillation in a plasmonic microring resonator containing quantum dots fabricated by transfer printing. *Japanese Journal of Applied Physics*, **2017**, 56, 102001	1.4	4
562	Manipulation of dynamic nuclear spin polarization in single quantum dots by photonic environment engineering. *Physical Review B*, **2017**, 95,	3.3	1
561	Method for generating a photonic NOON state with quantum dots in coupled nanocavities. *Physical Review A*, **2017**, 96,	2.6	8
560	Temperature dependence of the single photon emission from interface-fluctuation GaN quantum dots. *Scientific Reports*, **2017**, 7, 16107	4.9	9
559	Circularly polarized vacuum field in three-dimensional chiral photonic crystals probed by quantum dot emission. *Physical Review B*, **2017**, 96,	3.3	7
558	UV/Ozone-assisted bonding for InAs/GaAs quantum dot lasers on Si **2017**,		1
557	Nanosecond-scale spectral diffusion in the single photon emission of a GaN quantum dot. *AIP Advances*, **2017**, 7, 125216	1.5	14
556	A photonic crystal nanocavity with a quantum dot active region embedded by MBE regrowth **2017**,		1

555	Double-stage guided-mode converter for pure TM-mode guiding in pillar photonic-crystal waveguide devices. *Optics Express*, **2017**, 25, 17995-18008	3.3	4
554	Thresholdless quantum dot nanolaser. *Optics Express*, **2017**, 25, 19981-19994	3.3	43
553	Direct modulation of 1.3 Ẽh quantum dot lasers on silicon at 60 °C. *Optics Express*, **2016**, 24, 18428-35	3.3	23
552	Yellow luminescence band in undoped GaN revealed by two-wavelength excited photoluminescence. *Optical Materials*, **2016**, 60, 481-486	3.3	27
551	p-shell carrier assisted dynamic nuclear spin polarization in single quantum dots at zero external magnetic field. *Physical Review B*, **2016**, 93,	3.3	3
550	Electroluminescence at 1.3 μm from InAs/GaAs quantum dots monolithically grown on Ge/Si substrate by metal organic chemical vapor deposition. *Japanese Journal of Applied Physics*, **2016**, 55, 100304	1.4	2
549	Room-Temperature Observation of Trapped Exciton-Polariton Emission in GaN/AlGaN Microcavities with Air-Gap/III-Nitride Distributed Bragg Reflectors. *ACS Photonics*, **2016**, 3, 1182-1187	6.3	14
548	Single Photons from a Hot Solid-State Emitter at 350 K. *ACS Photonics*, **2016**, 3, 543-546	6.3	61
547	Linearly polarized single photons from small site-controlled GaN nanowire quantum dots **2016**,		3
546	Semiconductor Three-Dimensional Photonic Crystals with Novel Layer-by-Layer Structures. *Photonics*, **2016**, 3, 34	2.2	2
545	P-117 Phase II study of combination chemotherapy of gemcitabine/S-1 with nafamostat mesilate for advanced unresectable pancreatic cancer. First report. *Annals of Oncology*, **2016**, 27, ii34	10.3	78
544	Self-assembled formation of GaAsP nano-apertures above InAs/GaAs quantum dots by the thermal diffusion of phosphorus. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 659-663	1.3	2
543	InAs/GaAs quantum dot lasers with GaP strain-compensation layers grown by molecular beam epitaxy. *Physica Status Solidi (A) Applications and Materials Science*, **2016**, 213, 958-964	1.6	7
542	Single-photon emission at 1.5 Ẽh from an InAs/InP quantum dot with highly suppressed multi-photon emission probabilities. *Applied Physics Letters*, **2016**, 109, 132106	3.4	52
541	A Nanowire-Based Plasmonic Quantum Dot Laser. *Nano Letters*, **2016**, 16, 2845-50	11.5	53
540	Vacuum Rabi spectra of a single quantum emitter. *Physical Review Letters*, **2015**, 114, 143603	7.4	23
539	Direct Observation of Two-Step Photon Absorption in an InAs/GaAs Single Quantum Dot for the Operation of Intermediate-Band Solar Cells. *Nano Letters*, **2015**, 15, 4483-7	11.5	23
538	Room-temperature lasing in a single nanowire with quantum dots. *Nature Photonics*, **2015**, 9, 501-505	33.9	132

537	First Demonstration of Athermal Silicon Optical Interposers With Quantum Dot Lasers Operating up to 125 °C. *Journal of Lightwave Technology*, **2015**, 33, 1223-1229	4	57
536	InAs/GaAs Quantum Dot Lasers on Silicon-on-Insulator Substrates by Metal-Stripe Wafer Bonding. *IEEE Photonics Technology Letters*, **2015**, 27, 875-878	2.2	23
535	Doping dependent blue shift and linewidth broadening of intersubband absorption in non-polar m-plane AlGaN/GaN multiple quantum wells. *Applied Physics Letters*, **2015**, 107, 112107	3.4	20
534	High quality-factor Si/SiO(2)-InP hybrid micropillar cavities with submicrometer diameter for 1.55-μm telecommunication band. *Optics Express*, **2015**, 23, 16264-72	3.3	5
533	Asymmetric out-of-plane power distribution in a two-dimensional photonic crystal nanocavity. *Optics Letters*, **2015**, 40, 3372-5	3	5
532	Eigenvalue decomposition method for photon statistics of frequency-filtered fields and its application to quantum dot emitters. *Physical Review A*, **2015**, 92,	2.6	7
531	Effect of lateral electric field on the transition energies of neutral and charged excitons in In0.5Ga0.5As/GaAs quantum dots. *Physical Review B*, **2015**, 91,	3.3	5
530	Spectral diffusion and its influence on the emission linewidths of site-controlled GaN nanowire quantum dots. *Physical Review B*, **2015**, 92,	3.3	45
529	Strong coupling in non-polar GaN/AlGaN microcavities with air-gap/III-nitride distributed Bragg reflectors. *Applied Physics Letters*, **2015**, 107, 101102	3.4	19
528	Quantum key distribution over 120 km using ultrahigh purity single-photon source and superconducting single-photon detectors. *Scientific Reports*, **2015**, 5, 14383	4.9	101
527	A direct evidence of allocating yellow luminescence band in undoped GaN by two-wavelength excited photoluminescence. *Applied Physics Letters*, **2015**, 107, 212102	3.4	18
526	Excess carrier lifetime in epitaxially grown layers of germanium on silicon **2015**,		2
525	Dominant nonradiative centers in InGaN single quantum well by time-resolved and two-wavelength excited photoluminescence. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 952-955	1.3	4
524	Quantum Dot Laser for a Light Source of an Athermal Silicon Optical Interposer. *Photonics*, **2015**, 2, 355-364	2.2	3
523	Optical Characteristics of a Multichannel Hybrid Integrated Light Source for Ultra-High-Bandwidth Optical Interconnections. *Photonics*, **2015**, 2, 1131-1138	2.2	2
522	Low-Threshold near-Infrared GaAs–AlGaAs Core–Shell Nanowire Plasmon Laser. *ACS Photonics*, **2015**, 2, 165-171	6.3	75
521	Probing the excitonic states of site-controlled GaN nanowire quantum dots. *Nano Letters*, **2015**, 15, 1047-51	13.1	9
520	A Hybrid Integrated Light Source on a Silicon Platform Using a Trident Spot-Size Converter. *Journal of Lightwave Technology*, **2014**, 32, 1329-1336	4	94

519	Room-temperature triggered single photon emission from a III-nitride site-controlled nanowire quantum dot. *Nano Letters*, **2014**, 14, 982-6	11.5	285
518	1064-nm DFB laser diode modules applicable to seeder for pulse-on-demand fiber laser systems. *Optical Fiber Technology*, **2014**, 20, 714-724	2.4	7
517	(Invited) Si Waveguide-Integrated High-Speed Ge Photodetector. *ECS Transactions*, **2014**, 64, 723-727	1	1
516	Excitonic complexes in single zinc-blende GaN/AlN quantum dots grown by droplet epitaxy. *Applied Physics Letters*, **2014**, 105, 141112	3.4	8
515	InAs/GaAs quantum dot lasers metal-stripe-bonded onto SOI substrate **2014**,		1
514	Optical anisotropy of m -plane nitride air-gap distributed Bragg reflector microcavities. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 840-843		1
513	Measuring the second-order coherence of a nanolaser by intracavity frequency doubling. *Physical Review A*, **2014**, 89,	2.6	11
512	Multi-channel Hybrid Integrated Light Source for Ultra-high-bandwidth Optical Interconnections and Its Structural Optimization for Low Power Consumption by Considering Thermal Interference between LD Arrays. *Transactions of the Japan Institute of Electronics Packaging*, **2014**, 7, 94-103	0.3	4
511	Observation of mid-infrared intersubband absorption in non-polar m-plane AlGaN/GaN multiple quantum wells. *Applied Physics Letters*, **2014**, 105, 261108	3.4	25
510	Polarization properties of single zinc-blende GaN/AlN quantum dots. *Physical Review B*, **2014**, 90,	3.3	8
509	Athermal silicon optical interposers with quantum dot lasers operating from 25 to 125°C. *Electronics Letters*, **2014**, 50, 1377-1378	1.1	
508	Position-controlled InP nanowires with 10–100 μm pitches using Au-deposited SiO2/InP patterned substrates. *Applied Physics Letters*, **2014**, 104, 063102	3.4	16
507	High-density and wide-bandwidth optical interconnects with silicon optical interposers [Invited]. *Photonics Research*, **2014**, 2, A1	6	32
506	Manifestation of unconventional biexciton states in quantum dots. *Nature Communications*, **2014**, 5, 5721	17.4	36
505	Single-photon emission from cubic GaN quantum dots. *Applied Physics Letters*, **2014**, 104, 011101	3.4	39
504	Impact of the dark path on quantum dot single photon emitters in small cavities. *Physical Review Letters*, **2014**, 113, 143604	7.4	4
503	Highly uniform, multi-stacked InGaAs/GaAs quantum dots embedded in a GaAs nanowire. *Applied Physics Letters*, **2014**, 105, 103104	3.4	20
502	Spectral diffusion in nitride quantum dots: Emission energy dependent linewidths broadening via giant built-in dipole moments. *Physica Status Solidi - Rapid Research Letters*, **2014**, 8, 408-413	2.5	28

501	Identification of electric dipole moments of excitonic complexes in nitride-based quantum dots. *Physical Review B*, **2013**, 88,	3.3	23
500	Measurement of an exciton Rabi rotation in a single GaN/Al(x)Ga(1-x)N nanowire-quantum dot using photoluminescence spectroscopy: evidence for coherent control. *Physical Review Letters*, **2013**, 111, 057401	7.4	25
499	Narrow spectral linewidth of single zinc-blende GaN/AlN self-assembled quantum dots. *Applied Physics Letters*, **2013**, 103, 151109	3.4	20
498	Strong exciton confinement in site-controlled GaN quantum dots embedded in nanowires. *Applied Physics Letters*, **2013**, 103, 171907	3.4	23
497	Site-controlled growth of single GaN quantum dots in nanowires by MOCVD. *Journal of Crystal Growth*, **2013**, 370, 328-331	1.6	23
496	Theoretical analysis of multilevel intermediate-band solar cells using a drift diffusion model. *Journal of Applied Physics*, **2013**, 113, 243102	2.5	6
495	Temperature Dependent Photoluminescence Excitation Spectroscopy of GaN Quantum Dots in Site Controlled GaN/AlGaN Nanowires. *Japanese Journal of Applied Physics*, **2013**, 52, 08JL02	1.4	6
494	Growth of high-quality InAs quantum dots embedded in GaAs nanowire structures on Si substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1496-1499		5
493	High performance inkjet-printed C60 fullerene thin-film transistors: Toward a low-cost and reproducible solution process. *Organic Electronics*, **2013**, 14, 644-648	3.5	20
492	Rim formation on non-elongated InAs quantum dots grown by partial cap and annealing process at low temperature. *Journal of Crystal Growth*, **2013**, 378, 558-561	1.6	1
491	Non-VLS growth of GaAs nanowires on silicon by a gallium pre-deposition technique. *Journal of Crystal Growth*, **2013**, 378, 562-565	1.6	3
490	Molecular beam epitaxial growths of high-optical-gain InAs quantum dots on GaAs for long-wavelength emission. *Journal of Crystal Growth*, **2013**, 378, 459-462	1.6	26
489	Formation and optical properties of multi-stack InGaAs quantum dots embedded in GaAs nanowires by selective metalorganic chemical vapor deposition. *Journal of Crystal Growth*, **2013**, 370, 299-302	1.6	4
488	Shape evolution of low density InAs quantum dots in the partial capping process by using As2 source. *Journal of Crystal Growth*, **2013**, 378, 549-552	1.6	2
487	Growth of high-density 1.06-Ìm InGaAs/GaAs quantum dots for high gain lasers by molecular beamepitaxy. *Journal of Crystal Growth*, **2013**, 378, 627-630	1.6	9
486	Design of large-bandwidth single-mode operation waveguides in silicon three-dimensional photonic crystals using two guided modes. *Optics Express*, **2013**, 21, 12443-50	3.3	2
485	Nanocavity-based self-frequency conversion laser. *Optics Express*, **2013**, 21, 19778-89	3.3	21
484	Differential receivers with highly -uniform MSM Germanium photodetectors capped by SiGe layer. *Optics Express*, **2013**, 21, 23295-306	3.3	8

483	Development of high-density single-mode polymer waveguides with low crosstalk for chip-to-chip optical interconnection. *Optics Express*, **2013**, 21, 24231-9	3.3	15
482	Giant optical rotation in a three-dimensional semiconductor chiral photonic crystal. *Optics Express*, **2013**, 21, 29905-13	3.3	17
481	Design of Si/SiO2 micropillar cavities for Purcell-enhanced single photon emission at 1.55 Ìm from InAs/InP quantum dots. *Optics Letters*, **2013**, 38, 3241-4	3	11
480	Self-frequency summing in quantum dot photonic crystal nanocavity lasers. *Applied Physics Letters*, **2013**, 103, 243115	3.4	7
479	Fabrication and optical properties of non-polar III-nitride air-gap distributed Bragg reflector microcavities. *Applied Physics Letters*, **2013**, 103, 201118	3.4	18
478	Enhancement of Valence Band Mixing in Individual InAs/GaAs Quantum Dots by Rapid Thermal Annealing. *Japanese Journal of Applied Physics*, **2013**, 52, 125001	1.4	9
477	Photoluminescence Excitation Spectroscopy on Single GaN Quantum Dots. *Applied Physics Express*, **2013**, 6, 012102	2.4	11
476	Short-channel, high-mobility organic thin-film transistors with alkylated dinaphthothienothiophene. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1632-1635		13
475	Design of high-Q nanocavity in three-dimensional woodpile photonic crystal with vertically mirror-symmetric structure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1457-1460		1
474	High-Q AlN ladder-structure photonic crystal nanocavity fabricated by layer transfer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1517-1520		3
473	Cavity Quantum Electrodynamics in Semiconductors: Quantum Dot-Photonic Crystal Nanocavity Coupled Systems. *The Review of Laser Engineering*, **2013**, 41, 485	0	
472	Polarization-Insensitive Quantum Dot Semiconductor Optical Amplifiers Using Strain-Controlled Columnar Quantum Dots. *Journal of Lightwave Technology*, **2012**, 30, 68-75	4	22
471	Silicon-based three-dimensional photonic crystal nanocavity laser with InAs quantum-dot gain. *Applied Physics Letters*, **2012**, 101, 191107	3.4	7
470	Thin-film InAs/GaAs quantum dot solar cells layer-transferred onto Si substrates and flexible plastic films **2012**,		15
469	Flexible thin-film InAs/GaAs quantum dot solar cells. *Applied Physics Letters*, **2012**, 100, 192102	3.4	30
468	Improved stability in N-alkylated organic semiconductors for thin film transistors: Synthesis and characterization of N,N?-dialkylated dihydrodiazapentacene derivatives. *Synthetic Metals*, **2012**, 162, 1264-1270	3.6	10
467	Selective-area growth of thin GaN nanowires by MOCVD. *Journal of Crystal Growth*, **2012**, 357, 58-61	1.6	87
466	. *IEEE Journal of Selected Topics in Quantum Electronics*, **2012**, 18, 1818-1829	3.8	26

465	High-Q AlN photonic crystal nanobeam cavities fabricated by layer transfer. *Applied Physics Letters*, **2012**, 101, 101106	3.4	25
464	Exciton acoustic-phonon coupling in single GaN/AlN quantum dots. *Physical Review B*, **2012**, 85,	3.3	40
463	Influence of p-doping on the temperature dependence of InAs/GaAs quantum dot excited state radiative lifetime. *Applied Physics Letters*, **2012**, 101, 183108	3.4	5
462	Self-assembled m -plane InGaN quantum dots: formation and shape evolution. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 613-615		6
461	Surface Modification of Polydimethylsiloxane Using Low Pressure Chemical Vapour Deposition of Poly-Chloro-p-Xylene. *Journal of Nano Research*, **2012**, 20, 129-142	1	2
460	Fabrication of AlGaN Two-Dimensional Photonic Crystal Nanocavities by Selective Thermal Decomposition of GaN. *Applied Physics Express*, **2012**, 5, 126502	2.4	28
459	Demonstration of 12.5-Gbps optical interconnects integrated with lasers, optical splitters, optical modulators and photodetectors on a single silicon substrate. *Optics Express*, **2012**, 20, B256-63	3.3	40
458	1.3 μm InAs/GaAs quantum dot lasers on Si rib structures with current injection across direct-bonded GaAs/Si heterointerfaces. *Optics Express*, **2012**, 20, B315-21	3.3	15
457	High Q H1 photonic crystal nanocavities with efficient vertical emission. *Optics Express*, **2012**, 20, 28292-300	3.3	32
456	High-efficiency InAs/GaAs quantum dot solar cells by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2012**, 100, 193905	3.4	88
455	High guided mode–cavity mode coupling for an efficient extraction of spontaneous emission of a single quantum dot embedded in a photonic crystal nanobeam cavity. *Physical Review B*, **2012**, 86,	3.3	10
454	Site-controlled formation of InAs/GaAs quantum-dot-in-nanowires for single photon emitters. *Applied Physics Letters*, **2012**, 100, 263101	3.4	40
453	Spectral fluctuations of excitonic transitions of InGaAs single quantum dots. *Applied Physics Letters*, **2012**, 100, 022105	3.4	5
452	Enhancement of carbon nanotube photoluminescence by photonic crystal nanocavities. *Applied Physics Letters*, **2012**, 101, 141124	3.4	50
451	High-Q (>5000) AlN nanobeam photonic crystal cavity embedding GaN quantum dots. *Applied Physics Letters*, **2012**, 100, 121103	3.4	22
450	Enhancement of Light Emission from Silicon by Utilizing Photonic Nanostructures. *IEICE Transactions on Electronics*, **2012**, E95-C, 206-212	0.4	5
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